

# Vladimir Markevich

## List of Publications by Year in descending order

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3,001  
citations

186265

28  
h-index

254184

43  
g-index

201  
all docs

201  
docs citations

201  
times ranked

1280  
citing authors

#	ARTICLE	IF	CITATIONS
1	Electronic Properties and Structure of Boron-Hydrogen Complexes in Crystalline Silicon. Solar Rrl, 2022, 6, 2100459.	5.8	7
2	Dynamics of Hydrogen in Silicon at Finite Temperatures from First Principles. Physica Status Solidi (B): Basic Research, 2022, 259, .	1.5	7
3	Interactions of Hydrogen Atoms with Acceptor-Dioxygen Complexes in Czochralski-Grown Silicon. Physica Status Solidi (A) Applications and Materials Science, 2022, 219, .	1.8	2
4	Direct observation of hydrogen at defects in multicrystalline silicon. Progress in Photovoltaics: Research and Applications, 2021, 29, 1158-1164.	8.1	9
5	On the Correlation between Light-Induced Degradation and Minority Carrier Traps in Boron-Doped Czochralski Silicon. ACS Applied Materials & Interfaces, 2021, 13, 6140-6146.	8.0	3
6	Electrical Characterization of Thermally Activated Defects in n-Type Float-Zone Silicon. IEEE Journal of Photovoltaics, 2021, 11, 26-35.	2.5	8
7	Influence of isotopic composition of silicon on local vibrational modes of vacancy-oxygen complex. Journal of the Belarusian State University Physics, 2021, , 102-110.	0.2	0
8	Passivation of thermally-induced defects with hydrogen in float-zone silicon. Journal Physics D: Applied Physics, 2021, 54, 275105.	2.8	6
9	GaN surface sputter damage investigated using deep level transient spectroscopy. Materials Science in Semiconductor Processing, 2021, 126, 105654.	4.0	2
10	Calibrations coefficients for determination of concentrations of vacancy-oxygen-related complexes and oxygen dimer in silicon by means of infrared absorption spectroscopy. Proceedings of the National Academy of Sciences of Belarus Physical-Technical Series, 2021, 66, 227-233.	0.1	0
11	Acceptor-oxygen defects in silicon: The electronic properties of centers formed by boron, gallium, indium, and aluminum interactions with the oxygen dimer. Journal of Applied Physics, 2021, 130, 245703.	2.5	5
12	Formation of Oxygen-Containing Centers in Irradiated Silicon Crystals during Annealing in the Temperature Range of 450-700°C. Inorganic Materials: Applied Research, 2020, 11, 1078-1082.	0.5	1
13	Kinetics of Bulk Lifetime Degradation in Float-Zone Silicon: Fast Activation and Annihilation of Grown-In Defects and the Role of Hydrogen versus Light. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 2000436.	1.8	12
14	Characterisation of negative-U defects in semiconductors. Journal of Physics Condensed Matter, 2020, 32, 323001.	1.8	19
15	Local vibrational modes of vacancy-oxygen-related complexes at room temperature. Proceedings of the National Academy of Sciences of Belarus Physics and Mathematics Series, 2020, 56, 480-487.	0.2	1
16	Minority carrier traps in Czochralski-grown p-type silicon crystals doped with B, Al, Ga, or In impurity atoms. , 2020, , .		0
17	Boron-Hydrogen Oxygen Complex Responsible for Light-Induced Degradation in Silicon Photovoltaic Cells: A New Insight into the Problem. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900315.	1.8	23
18	Transformation of Structural Defects and The Hydrogen State Upon Heat Treatment of Hydrogenated Silicon. Journal of Applied Spectroscopy, 2019, 86, 822-824.	0.7	2

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19	New insights into the thermally activated defects in n-type float-zone silicon. AIP Conference Proceedings, 2019, , .	0.4	13
20	Identification of the mechanism responsible for the boron oxygen light induced degradation in silicon photovoltaic cells. Journal of Applied Physics, 2019, 125, .	2.5	36
21	Evidence for Molybdenum-Hydrogen Bonding in p-Type Silicon upon Annealing under Illumination. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800611.	1.8	3
22	Interaction of Radiation-Induced Self-Interstitials with Vacancy-Oxygen Related Defects $V_n O_2$ ( $n$ from) $T_j$ $E_{Tj}$ $O_{0.0}$ $rg$ $BT$ /Overlo	1.8	8
23	Tutorial: Junction spectroscopy techniques and deep-level defects in semiconductors. Journal of Applied Physics, 2018, 123, .	2.5	82
24	Lifetime degradation of n-type Czochralski silicon after hydrogenation. Journal of Applied Physics, 2018, 123, .	2.5	4
25	Acceptor levels of the carbon vacancy in 4H-SiC: Combining Laplace deep level transient spectroscopy with density functional modeling. Journal of Applied Physics, 2018, 124, 245701.	2.5	19
26	Electron emission and capture by oxygen-related bistable thermal double donors in silicon studied with junction capacitance techniques. Journal of Applied Physics, 2018, 124, .	2.5	14
27	Thermally activated defects in float zone silicon: Effect of nitrogen on the introduction of deep level states. Journal of Applied Physics, 2018, 124, .	2.5	19
28	Optical Properties and the Mechanism of the Formation of $V_2O_2$ and $V_3O_2$ Vacancy-Oxygen Complexes in Irradiated Silicon Crystals. Semiconductors, 2018, 52, 1097-1103.	0.5	6
29	Radiation-induced interstitial carbon atom in silicon: Effect of charge state on annealing characteristics. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700262.	1.8	5
30	Vanadium in silicon: Lattice positions and electronic properties. Applied Physics Letters, 2017, 110, 142105.	3.3	4
31	Recombination via transition metals in solar silicon: The significance of hydrogen-metal reactions and lattice sites of metal atoms. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700304.	1.8	11
32	Theory of a carbon-oxygen-hydrogen recombination center in n-type Si. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700309.	1.8	6
33	Powerful recombination centers resulting from reactions of hydrogen with carbon-oxygen defects in n-type Czochralski-grown silicon. Physica Status Solidi - Rapid Research Letters, 2017, 11, 1700133.	2.4	13
34	The di-interstitial in silicon: Electronic properties and interactions with oxygen and carbon impurity atoms. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700261.	1.8	6
35	Permanent annihilation of thermally activated defects which limit the lifetime of float-zone silicon. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 2844-2849.	1.8	69
36	Interactions of hydrogen with vanadium in crystalline silicon. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 2838-2843.	1.8	6

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37	Local vibrational modes of interstitial boron–interstitial oxygen complex in silicon. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 2850-2854.	1.8	5
38	Recombination centers resulting from reactions of hydrogen and oxygen in n-type Czochralski silicon. , 2016, , .		4
39	Exceptional gettering response of epitaxially grown kerfless silicon. Journal of Applied Physics, 2016, 119, .	2.5	9
40	Gettering of interstitial iron in silicon by plasma-enhanced chemical vapour deposited silicon nitride films. Journal of Applied Physics, 2016, 120, .	2.5	52
41	Thermally stable carbon–oxygen complexes in irradiated silicon crystals. Inorganic Materials: Applied Research, 2016, 7, 192-195.	0.5	2
42	Formation of donors in germanium–silicon alloys implanted with hydrogen ions with different energies. Semiconductors, 2016, 50, 1122-1124.	0.5	0
43	Thermal activation and deactivation of grown–in defects limiting the lifetime of float–zone silicon. Physica Status Solidi - Rapid Research Letters, 2016, 10, 443-447.	2.4	82
44	Radiation-induced bistable centers with deep levels in silicon n +p structures. Semiconductors, 2016, 50, 751-755.	0.5	10
45	Electrical and Optical Defect Evaluation Techniques for Electronic and Solar Grade Silicon. Lecture Notes in Physics, 2015, , 129-180.	0.7	2
46	Evidence for an iron-hydrogen complex in p-type silicon. Applied Physics Letters, 2015, 107, .	3.3	19
47	Molybdenum nano-precipitates in silicon: A TEM and DLTS study. Physica Status Solidi (B): Basic Research, 2014, 251, 2201-2204.	1.5	7
48	Donor levels of the divacancy-oxygen defect in silicon. Journal of Applied Physics, 2014, 115, 012004.	2.5	13
49	Titanium in silicon: Lattice positions and electronic properties. Applied Physics Letters, 2014, 104, 152105.	3.3	20
50	Divacancy-iron complexes in silicon. Journal of Applied Physics, 2013, 113, 044503.	2.5	4
51	$E_1$ / $E_2$ traps in 6H-SiC studied with Laplace deep level transient spectroscopy. Applied Physics Letters, 2013, 102, .	3.3	12
52	Passivation of titanium by hydrogen in silicon. Applied Physics Letters, 2013, 103, 132103.	3.3	19
53	Recombination via point defects and their complexes in solar silicon. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1884-1893.	1.8	42
54	Reconfigurations and diffusion of trivacancy in silicon. Physica B: Condensed Matter, 2012, 407, 2974-2977.	2.7	2

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55	Laplace deep level transient spectroscopy: Embodiment and evolution. <i>Physica B: Condensed Matter</i> , 2012, 407, 3026-3030.	2.7	13
56	Electronic and dynamical properties of the silicon trivacancy. <i>Physical Review B</i> , 2012, 86, .	3.2	35
57	Formation and annealing of radiation defects in tin-doped p-type germanium crystals. <i>Semiconductors</i> , 2012, 46, 611-614.	0.5	1
58	Tin-vacancy complex in germanium. <i>Journal of Applied Physics</i> , 2011, 109, .	2.5	27
59	Structure and electronic properties of trivacancy and trivacancy-oxygen complexes in silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011, 208, 568-571.	1.8	31
60	Local vibrational modes of the oxygen trimer in Si. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 709-712.	0.8	5
61	The oxygen dimer in Si: Its relationship to the light-induced degradation of Si solar cells?. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	45
62	Impedance and barrier capacitance of silicon diodes implanted with high-energy Xe ions. <i>Microelectronics Reliability</i> , 2010, 50, 813-820.	1.7	9
63	Interaction of copper atoms with radiation-induced defects in silicon. <i>Inorganic Materials</i> , 2010, 46, 333-338.	0.8	2
64	Interactions of Cu and Ni Impurities with Vacancy-related Point Defects in Czochralski-grown Si Crystals. <i>ECS Transactions</i> , 2009, 18, 1013-1018.	0.5	5
65	Energy state distributions at oxide-semiconductor interfaces investigated by Laplace DLTS. <i>Physica B: Condensed Matter</i> , 2009, 404, 4604-4607.	2.7	1
66	Trivacancy in silicon: A combined DLTS and ab-initio modeling study. <i>Physica B: Condensed Matter</i> , 2009, 404, 4565-4567.	2.7	8
67	Relation between photocurrent and DLTS signals observed for quantum dot systems. <i>Physica B: Condensed Matter</i> , 2009, 404, 5170-5172.	2.7	0
68	Defect-impurity complexes with high thermal stability in epi-Si n+-p diodes irradiated with MeV electrons. <i>Vacuum</i> , 2009, 83, S131-S133.	3.5	1
69	Neutron-irradiation-induced defects in germanium: A Laplace deep level transient spectroscopy study. <i>Vacuum</i> , 2009, 84, 32-36.	3.5	1
70	Trivacancy-oxygen complex in silicon: Local vibrational mode characterization. <i>Physica B: Condensed Matter</i> , 2009, 404, 4568-4571.	2.7	11
71	Interstitial-related defect reactions in electron-irradiated oxygen-rich Ge crystals: A DLTS study. <i>Physica B: Condensed Matter</i> , 2009, 404, 4533-4536.	2.7	4
72	Trivacancy and trivacancy-oxygen complexes in silicon: Experiments and ab initio modeling. <i>Physical Review B</i> , 2009, 80, .	3.2	55

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73	Formation of Hydrogen-Related Shallow Donors in Ge <sub>1-x</sub> Si <sub>x</sub> Crystals Implanted with Protons. Solid State Phenomena, 2008, 131-133, 131-136.	0.3	1
74	Radiation-Induced Defect Reactions in Cz-Si Crystals Contaminated with Cu. Solid State Phenomena, 2008, 131-133, 363-368.	0.3	13
75	Piezospectroscopic analysis of mobile defects in semiconducting materials. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 529-534.	0.8	0
76	Complexes of self-interstitials with oxygen atoms in germanium. Materials Science in Semiconductor Processing, 2008, 11, 344-347.	4.0	5
77	Implantation defects and n-type doping in Ge and Ge rich SiGe. Thin Solid Films, 2008, 517, 152-154.	1.8	17
78	Electrically active hydrogen-implantation-induced defects in Ge crystals and SiGe alloys. Thin Solid Films, 2008, 517, 419-421.	1.8	3
79	Electrically active defects induced by hydrogen and helium implantations in Ge. Materials Science in Semiconductor Processing, 2008, 11, 354-359.	4.0	4
80	Bistability of hydrogen donors in proton-implanted GeSi alloy. Technical Physics Letters, 2008, 34, 498-499.	0.7	1
81	Energy state distributions of the Pb centers at the (100), (110), and (111) Si <sup>*</sup> •SiO <sub>2</sub> interfaces investigated by Laplace deep level transient spectroscopy. Applied Physics Letters, 2008, 92, .	3.3	25
82	Formation of interstitial carbon- <sup>*</sup> interstitial oxygen complexes in silicon: Local vibrational mode spectroscopy and density functional theory. Physical Review B, 2008, 78, .	3.2	23
83	Evolution of vacancy-related defects upon annealing of ion-implanted germanium. Physical Review B, 2008, 78, .	3.2	22
84	Hole-Related Electrical Activity of InAs/GaAs Quantum Dots. Acta Physica Polonica A, 2008, 114, 1201-1206.	0.5	1
85	Alloy shift of <sup>*</sup> germanium- <sup>*</sup> iron-related electronic levels in unstrained silicon-germanium alloys. Physical Review B, 2007, 76, .	3.2	2
86	Influence of electron irradiation on characteristics of Si <sub>1-x</sub> Ge <sub>x</sub> n-structures. Vacuum, 2007, 81, 1171-1174.	3.5	0
87	Electrically active defects induced by irradiations with electrons, neutrons and ions in Ge-rich SiGe alloys. Physica B: Condensed Matter, 2007, 401-402, 184-187.	2.7	3
88	Identification of stable and metastable forms of centers in germanium. Physica B: Condensed Matter, 2007, 401-402, 192-195.	2.7	4
89	Electron- and hole-related electrical activity of InAs/GaAs quantum dots. Physica B: Condensed Matter, 2007, 401-402, 580-583.	2.7	6
90	Effect of high-temperature heat treatment on the generation and annealing of radiation-induced defects in n-type silicon crystals. Inorganic Materials, 2007, 43, 1153-1159.	0.8	3

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91	Iron-aluminium pair reconfiguration processes in SiGe alloys. Journal of Materials Science: Materials in Electronics, 2007, 18, 759-762.	2.2	5
92	Radiation Performance of Ge Technologies. , 2007, , 211-232.		0
93	Germanium – The Semiconductor of Tomorrow?. AIP Conference Proceedings, 2006, , .	0.4	4
94	Determination of interstitial oxygen concentration in germanium by infrared absorption. Journal of Applied Physics, 2006, 100, 033525.	2.5	14
95	Phonon-assisted changes in charge states of deep level defects in germanium. Physica B: Condensed Matter, 2006, 376-377, 61-65.	2.7	3
96	The different behaviour of CiOi and CiCs defects in SiGe. Materials Science in Semiconductor Processing, 2006, 9, 58-61.	4.0	2
97	Oxygen loss and thermal double donor formation in germanium. Materials Science in Semiconductor Processing, 2006, 9, 619-624.	4.0	3
98	Hydrogen-related shallow donors in Ge crystals implanted with protons. Materials Science in Semiconductor Processing, 2006, 9, 629-633.	4.0	4
99	Divacancy-related complexes in Si(1-x)Ge(x). Materials Science in Semiconductor Processing, 2006, 9, 525-530.	4.0	2
100	Defects induced by irradiation with fast neutrons in n-type germanium. Materials Science in Semiconductor Processing, 2006, 9, 606-612.	4.0	2
101	A comparative study of ion implantation and irradiation-induced defects in Ge crystals. Materials Science in Semiconductor Processing, 2006, 9, 589-596.	4.0	19
102	Interaction of self-interstitials with oxygen-related defects in electron-irradiated Ge crystals. Materials Science in Semiconductor Processing, 2006, 9, 613-618.	4.0	5
103	Evolution of radiation-induced carbon-oxygen-related defects in silicon upon annealing: LVM studies. Nuclear Instruments & Methods in Physics Research B, 2006, 253, 210-213.	1.4	27
104	High-resolution DLTS of vacancy-donor pairs in P-, As- and Sb-doped silicon. Physica B: Condensed Matter, 2006, 376-377, 73-76.	2.7	3
105	Vacancy defect reactions associated with oxygen and bismuth in irradiated germanium. Physica B: Condensed Matter, 2006, 376-377, 93-96.	2.7	3
106	Bistability and electrical activity of the vacancy-dioxygen complex in silicon. Semiconductors, 2006, 40, 1282-1286.	0.5	15
107	Electric field enhancement of electron emission from deep level traps in Ge crystals. Physica B: Condensed Matter, 2006, 376-377, 200-203.	2.7	9
108	Understanding Ion Implantation Defects in Germanium. ECS Transactions, 2006, 3, 67-76.	0.5	7

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109	Ion implantation and electron irradiation damage in unstrained germanium and silicon-germanium alloys. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005, 124-125, 166-169.	3.5	12
110	Metastable VO <sub>2</sub> Complexes in Silicon: Experimental and Theoretical Modeling Studies. <i>Solid State Phenomena</i> , 2005, 108-109, 223-228.	0.3	13
111	VO <sub>n</sub> (n=3) Defects in Irradiated and Heat-Treated Silicon. <i>Solid State Phenomena</i> , 2005, 108-109, 267-272.	0.3	34
112	Electronic Properties and Thermal Stability of Defects Induced by MeV Electron/Ion Irradiations in Unstrained Germanium and SiGe Alloys. <i>Solid State Phenomena</i> , 2005, 108-109, 253-260.	0.3	6
113	Electronic Properties and Structure of a Complex Incorporating a Self-Interstitial and two Oxygen Atoms in Silicon. <i>Solid State Phenomena</i> , 2005, 108-109, 273-278.	0.3	10
114	The vacancy-donor pair in unstrained silicon, germanium and SiGe alloys. <i>Journal of Physics Condensed Matter</i> , 2005, 17, S2293-S2302.	1.8	17
115	Thermal double donor annihilation and oxygen precipitation at around 650°C in Czochralski-grown Si: local vibrational mode studies. <i>Journal of Physics Condensed Matter</i> , 2005, 17, S2237-S2246.	1.8	25
116	Vacancy-related complexes in neutron-irradiated silicon. <i>Journal of Physics Condensed Matter</i> , 2005, 17, S2229-S2235.	1.8	14
117	Interstitial Carbon Related Defects in Low-Temperature Irradiated Si: FTIR and DLTS Studies. <i>Solid State Phenomena</i> , 2005, 108-109, 261-266.	0.3	14
118	Electrically active radiation-induced defects in Czochralski-grown Si with low carbon content. <i>Journal of Physics Condensed Matter</i> , 2005, 17, S2331-S2340.	1.8	16
119	Calibration Factor for Determination of Interstitial Oxygen Concentration in Germanium by Infrared Absorption. <i>Solid State Phenomena</i> , 2005, 108-109, 735-740.	0.3	4
120	Publisher's Note: Donor level of bond-center hydrogen in germanium [Phys. Rev. B69, 245207 (2004)]. <i>Physical Review B</i> , 2004, 70, .	3.2	7
121	Donor level of bond-center hydrogen in germanium. <i>Physical Review B</i> , 2004, 69, .	3.2	34
122	Electronic properties of antimony-vacancy complex in Ge crystals. <i>Journal of Applied Physics</i> , 2004, 95, 4078-4083.	2.5	77
123	Recombination and radiation damage in crystalline silicon solar cell material. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004, 1, 2274-2281.	0.8	2
124	Vacancy-group-V-impurity atom pairs in Ge crystals doped with P, As, Sb, and Bi. <i>Physical Review B</i> , 2004, 70, .	3.2	108
125	Structure and properties of vacancy-oxygen complexes in Si <sub>1-x</sub> Ge <sub>x</sub> alloys. <i>Physical Review B</i> , 2004, 69, .	3.2	42
126	Electronic properties of vacancy-oxygen complexes in SiGe alloys. <i>Physica B: Condensed Matter</i> , 2003, 340-342, 790-794.	2.7	5



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127	Vacancy-oxygen complex in Ge crystals. <i>Physica B: Condensed Matter</i> , 2003, 340-342, 844-848.	2.7	17
128	The VO <sub>2</sub> * defect in silicon. <i>Physica B: Condensed Matter</i> , 2003, 340-342, 509-513.	2.7	35
129	Spectroscopic observation of the TDD0 in silicon. <i>Physica B: Condensed Matter</i> , 2003, 340-342, 1046-1050.	2.7	9
130	Carbon-related centres in irradiated SiGe alloys. <i>Physica B: Condensed Matter</i> , 2003, 340-342, 823-826.	2.7	8
131	Defect-impurity interactions in irradiated tin-doped Cz-Si crystals. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 694-697.	0.8	13
132	Radiation-induced defects and their transformations in oxygen-rich germanium crystals. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 702-706.	0.8	23
133	Saddle point for oxygen reorientation in the vicinity of a silicon vacancy. <i>Physical Review B</i> , 2003, 67, .	3.2	13
134	Defect reactions associated with divacancy elimination in silicon. <i>Journal of Physics Condensed Matter</i> , 2003, 15, S2779-S2789.	1.8	52
135	Vacancy-oxygen complex in Si <sub>1-x</sub> Ge <sub>x</sub> crystals. <i>Applied Physics Letters</i> , 2003, 82, 2652-2654.	3.3	22
136	Oxygen-related radiation-induced defects in SiGe alloys. <i>Journal of Physics Condensed Matter</i> , 2003, 15, S2835-S2842.	1.8	8
137	Stable Hydrogen Pair Trapped at Carbon Impurities in Silicon. <i>Defect and Diffusion Forum</i> , 2003, 221-223, 1-10.	0.4	2
138	Electronic properties of vacancy-oxygen complex in Ge crystals. <i>Applied Physics Letters</i> , 2002, 81, 1821-1823.	3.3	68
139	Defect engineering in Czochralski silicon by electron irradiation at different temperatures. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 2002, 186, 121-125.	1.4	50
140	Local vibrational modes of the oxygen-vacancy complex in germanium. <i>Semiconductors</i> , 2002, 36, 621-624.	0.5	13
141	Interstitial carbon-oxygen center and hydrogen related shallow thermal donors in Si. <i>Physical Review B</i> , 2001, 65, .	3.2	75
142	Early stages of oxygen clustering in hydrogenated Cz-Si: IR absorption studies. <i>Physica B: Condensed Matter</i> , 2001, 302-303, 180-187.	2.7	11
143	Complexes of the self-interstitial with oxygen in irradiated silicon. <i>Physica B: Condensed Matter</i> , 2001, 302-303, 188-192.	2.7	31
144	Enhancement of thermal donor formation in germanium by preliminary irradiation: infrared absorption measurements. <i>Physica B: Condensed Matter</i> , 2001, 302-303, 201-205.	2.7	2

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145	Magnetic resonance studies of shallow donor centers in hydrogenated Cz-Si crystals. Physica B: Condensed Matter, 2001, 302-303, 212-219.	2.7	1
146	Cs-H <sub>2</sub> * defect in crystalline silicon. Physica B: Condensed Matter, 2001, 302-303, 220-226.	2.7	18
147	Magnetic resonance and FTIR studies of shallow donor centers in hydrogenated Cz-silicon. Physica B: Condensed Matter, 2001, 308-310, 253-256.	2.7	2
148	Interaction between self-interstitials and the oxygen dimer in silicon. Physica B: Condensed Matter, 2001, 308-310, 284-289.	2.7	31
149	Isotopic effects on vibrational modes of thermal double donors in Si and Ge. Physica B: Condensed Matter, 2001, 308-310, 290-293.	2.7	8
150	Evidence for trapped by carbon impurities in silicon. Physica B: Condensed Matter, 2001, 308-310, 197-201.	2.7	23
151	Defect reactions associated with the dissociation of the phosphorus-vacancy pair in silicon. Physica B: Condensed Matter, 2001, 308-310, 513-516.	2.7	11
152	Over-coordinated oxygen in the interstitial carbon-oxygen complex. Physica B: Condensed Matter, 2001, 308-310, 305-308.	2.7	7
153	Vibration modes of oxygen dimers in germanium. Semiconductors, 2001, 35, 864-869.	0.5	3
154	Carbon-Oxygen-Related Complexes in Irradiated and Heat-Treated Silicon: IR Absorption Studies. Solid State Phenomena, 2001, 82-84, 57-62.	0.3	28
155	Thermal Double Donors and Quantum Dots. Physical Review Letters, 2001, 87, 235501.	7.8	33
156	Response to "Comment on "Hydrogen-oxygen interaction in silicon at around 50°C". [J. Appl. Phys. 87, 4635 (2000)]. Journal of Applied Physics, 2000, 87, 4637-4637.	2.5	2
157	Photoluminescence characterization of defects created in electron-irradiated silicon at elevated temperatures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 72, 146-149.	3.5	5
158	Early stages of oxygen precipitation in silicon: The effect of hydrogen. Semiconductors, 2000, 34, 998-1003.	0.5	5
159	Local Vibrations of Oxygen-Containing Thermal Donors in Germanium. Journal of Applied Spectroscopy, 2000, 67, 904-909.	0.7	0
160	Hydrogen-plasma-enhanced oxygen precipitation in silicon. Journal of Physics Condensed Matter, 2000, 12, 10145-10152.	1.8	5
161	Observation and theory of the V <sub>Si</sub> -O-H <sub>2</sub> complex in silicon. Physical Review B, 2000, 61, 12964-12969.	3.2	22
162	Interaction of Hydrogen with Radiation-Induced Defects in Cz-Si Crystals. Solid State Phenomena, 1999, 69-70, 403-408.	0.3	2

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163	New Infrared Vibrational Bands Related to Interstitial and Substitutional Oxygen in Silicon. Solid State Phenomena, 1999, 69-70, 309-314.	0.3	11
164	Infrared Vibrational Bands Related to Thermal Donors in Germanium. Solid State Phenomena, 1999, 69-70, 303-308.	0.3	3
165	Oxygen and Carbon Clustering in Cz-Si during Electron Irradiation at Elevated Temperatures. Solid State Phenomena, 1999, 69-70, 297-302.	0.3	11
166	Vibrational absorption from vacancy-oxygen-related complexes (VO, V2O, VO2) in irradiated silicon. Physica B: Condensed Matter, 1999, 273-274, 291-295.	2.7	44
167	Local vibrational mode bands of Vâ€“Oâ€“H complexes in silicon. Physica B: Condensed Matter, 1999, 273-274, 300-304.	2.7	2
168	Effect of high-temperature electron irradiation on the formation of radiative defects in silicon. Physica B: Condensed Matter, 1999, 273-274, 528-531.	2.7	2
169	Local vibrational mode spectroscopy of thermal donors in germanium. Physica B: Condensed Matter, 1999, 273-274, 570-574.	2.7	11
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